

## **Description**

The DMP2120U-7 uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})}$ , This device is suitable

for use as a load switch or in PWM applications.



SOT-23

#### **General Features**

 $V_{DS} = -20V, I_{D} = -3A$ 

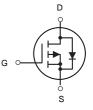
 $R_{DS(ON)}$  <  $80m\Omega$  @  $V_{GS}$ =-4.5V

## **Application**

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
DMP2120U-7	SOT-23	A1SHB	3000

## Absolute Maximum Ratings (TA=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	-3	А
Ірм	Drain Current-Pulsed (Note 1)	-10	А
P <sub>D</sub>	Maximum Power Dissipation	1	W
Тл,Твтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W

# P-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

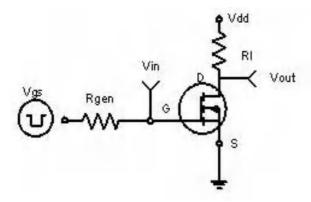
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	"		1	I	I	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20	-24	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	-1	μA
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=-250\mu A$	-0.4	-0.7	-1	V
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	60	80	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2A	-	85	103	mΩ
Forward Transconductance	grs	V <sub>DS</sub> =-5V,I <sub>D</sub> =-2A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>		-	405	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-10V,V <sub>GS</sub> =0V,	-	75	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	55	-	PF
Switching Characteristics (Note 4)	1					
Turn-on Delay Time	td(on)		-	11	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-10V,I <sub>D</sub> =-1A V <sub>GS</sub> =-	-	35	-	nS
Turn-Off Delay Time	td(off)	4.5V,R <sub>GEN</sub> =10Ω	-	30	-	nS
Turn-Off Fall Time	tf		-	10	-	nS
Total Gate Charge	Qg		-	3.3	12	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-10V, $I_D$ =-3A,	-	0.7	-	nC
Gate-Drain Charge	Qgd	V <sub>GS</sub> =-2.5V	-	1.3	-	nC
Drain-Source Diode Characteristics			1	ı	L	
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V, I <sub>S</sub> =1.3A	-	_	-1.2	V
Diode Forward Current (Note 2)	ls		-	-	-3	Α

### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# Typical Electrical and Thermal Characteristics



**Figure 1:Switching Test Circuit** 

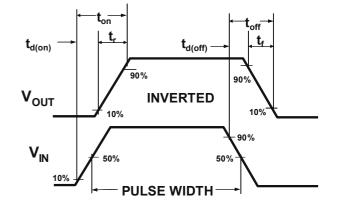
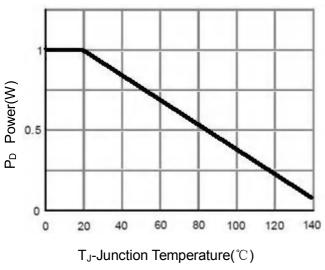


Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 

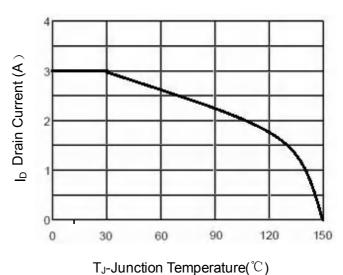
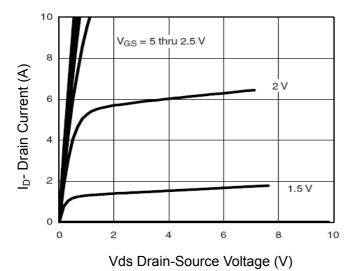


Figure 4 Drain Current



**Figure 5 Output Characteristics** 

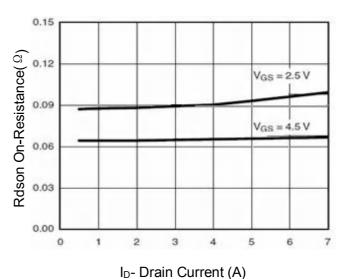
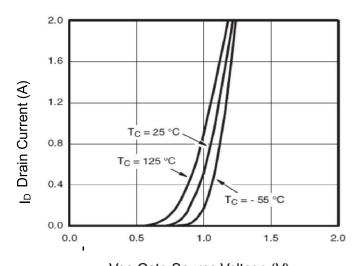
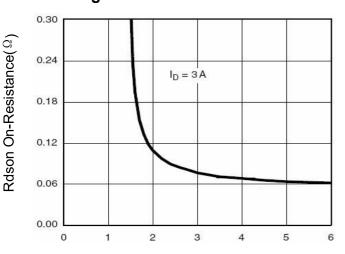


Figure 6 Drain-Source On-Resistance

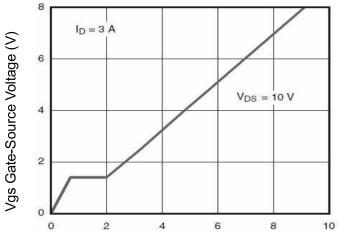




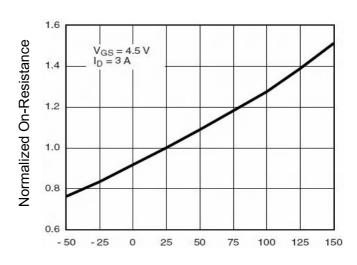
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



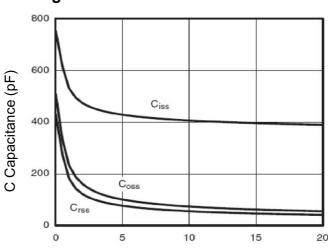
Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs



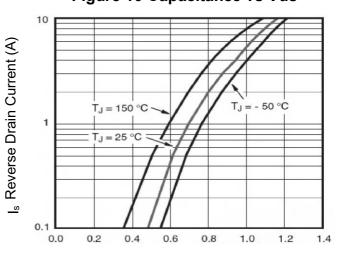
Qg Gate Charge (nC) Figure 11 Gate Charge



 $T_J$ -Junction Temperature( ${}^{\mathbb{C}}$ ) Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward

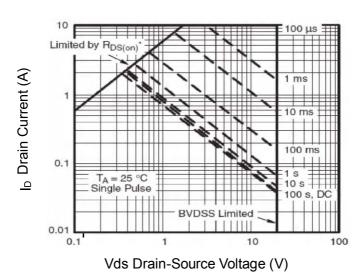
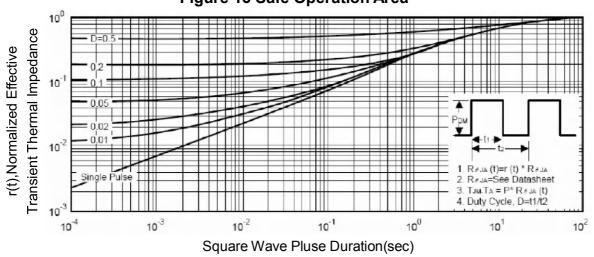


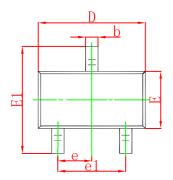
Figure 13 Safe Operation Area

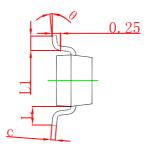


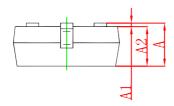
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Outline Dimensions**

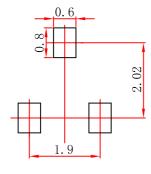






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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